

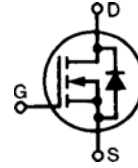
HiPerFET™ Power MOSFETs Q-Class

IXFK 52N60Q2
IXFX 52N60Q2

$V_{DSS} = 600\text{ V}$
 $I_{D25} = 52\text{ A}$
 $R_{DS(on)} = 115\text{ m}\Omega$

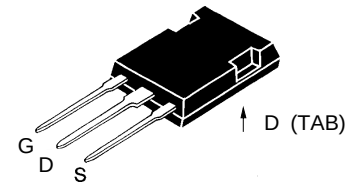
$t_{rr} \leq 250\text{ ns}$

N-Channel Enhancement Mode
Avalanche Rated, High dv/dt, Low Q_g
Low intrinsic R_g , low t_{rr}

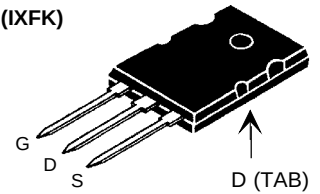


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{DGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GS} = 1\text{ M}\Omega$	600	V
V_{GS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	52	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	208	A
I_{AR}	$T_C = 25^\circ\text{C}$	52	A
E_{AR}	$T_C = 25^\circ\text{C}$	75	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	4.0	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2\text{ }\Omega$	20	V/ns
P_D	$T_C = 25^\circ\text{C}$	735	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s	300	$^\circ\text{C}$
M_d	Mounting torque	TO-264	0.9/6 Nm/lb.in.
Weight		PLUS-247	6 g
		TO-264	10 g

PLUS247™ (IXFX)



TO-264 AA (IXFK)



G = Gate
S = Source

D = Drain
TAB = Drain

Features

- Double metal process for low gate resistance
- International standard packages
- Epoxy meet UL 94 V-0, flammability classification
- Avalanche energy and current rated
- Fast intrinsic Rectifier

Advantages

- Easy to mount
- Space savings
- High power density

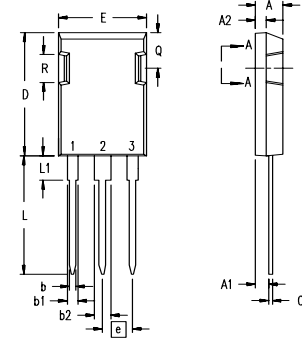
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 3\text{ mA}$	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8\text{ mA}$	2.0		4.5 V
I_{GSS}	$V_{GS} = \pm 20\text{ V}_{DC}$, $V_{DS} = 0$			$\pm 200\text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$, $T_J = 25^\circ\text{C}$ $V_{GS} = 0\text{ V}$, $T_J = 125^\circ\text{C}$			50 μA 2 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 0.5 \cdot I_{D25}$ Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $d \leq 2\%$			115 m Ω

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test	30	40	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		6800	pF
C_{oss}			1000	pF
C_{rss}			225	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1.0\ \Omega$ (External),		23	ns
t_r			13	ns
$t_{d(off)}$			56	ns
t_f			8.5	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		198	nC
Q_{gs}			43	nC
Q_{gd}			94	nC
R_{thJC}	TO-264			0.17 K/W
R_{thCK}			0.15	K/W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			52 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			208 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		1	250 ns
Q_{RM}			10	μC
I_{RM}				A

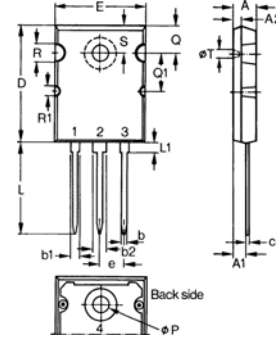
PLUS 247™ Outline



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)
4 - Drain (Collector)

Dim.	Millimeter Min. Max.	Inches Min. Max.
A	4.83 5.21	.190 .205
A ₁	2.29 2.54	.090 .100
A ₂	1.91 2.16	.075 .085
b	1.14 1.40	.045 .055
b ₁	1.91 2.13	.075 .084
b ₂	2.92 3.12	.115 .123
C	0.61 0.80	.024 .031
D	20.80 21.34	.819 .840
E	15.75 16.13	.620 .635
e	5.45 BSC	.215 BSC
L	19.81 20.32	.780 .800
L1	3.81 4.32	.150 .170
Q	5.59 6.20	.220 .244
R	4.32 4.83	.170 .190

TO-264 AA Outline



Dim.	Millimeter Min. Max.	Inches Min. Max.
A	4.82 5.13	.190 .202
A ₁	2.54 2.89	.100 .114
A ₂	2.00 2.10	.079 .083
b	1.12 1.42	.044 .056
b ₁	2.39 2.69	.094 .106
b ₂	2.90 3.09	.114 .122
c	0.53 0.83	.021 .033
D	25.91 26.16	1.020 1.030
E	19.81 19.96	.780 .786
e	5.46 BSC	.215 BSC
J	0.00 0.25	.000 .010
K	0.00 0.25	.000 .010
L	20.32 20.83	.800 .820
L1	2.29 2.59	.090 .102
P	3.17 3.66	.125 .144
Q	6.07 6.27	.239 .247
Q ₁	8.38 8.69	.330 .342
R	3.81 4.32	.150 .170
R ₁	1.78 2.29	.070 .090
S	6.04 6.30	.238 .248
T	1.57 1.83	.062 .072

IXYS reserves the right to change limits, test conditions, and dimensions.